

FIS9-2000-0404US1



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Heemyong Park, Fariborz Assaderaghi and Jack A. Mandelman

Serial No.: not assigned

Group Art Unit: not assigned

Filed:

Examiner: Not known

For: METHOD OF BUILDING A CMOS STRUCTURE ON THIN SOI WITH  
SOURCE/DRAIN ELECTRODES FORMED BY IN SITU DOPED  
SELECTIVE AMORPHOUS SILICON

Commissioner of Patents and Trademarks  
Washington, D.C. 20231

**INFORMATION DISCLOSURE STATEMENT  
UNDER 37 C.F.R. 1.56**

Sir:

Under the provisions of 37 C.F.R. 1.97 through 1.99 and pursuant to applicant's duty of disclosure under 37 C.F.R. 1.56, applicant respectfully brings the documents listed on the attached form PTO-1449, and discussed in the Specification, to the attention of the Examiner in charge of the above-identified application. Copies of these documents are provided herewith for the convenience of the Examiner.

This citation does not constitute an admission that the references are relevant or material to the claims. They are merely cited as constituting related art of which the applicant is aware.

It is respectfully requested that these documents be considered by the Examiner and formally made of record in this application.

FIS9-2000-0404US1

Respectfully submitted,

*Marshall M. Curtis*

Marshall M. Curtis

Reg. No. 33,138

McGuireWoods LLP  
1750 Tysons Blvd., Suite 1800  
McLean, VA 22102  
(703) 712-5062

EXPRESS MAIL NO.: EF383029816US

I HEREBY CERTIFY THAT THIS CORRESPONDENCE IS BEING  
DEPOSITED WITH THE U.S. POSTAL SERVICE AS EXPRESS  
MAIL IN AN ENVELOPE ADDRESSED TO: COMMISSIONER OF  
PATENTS AND TRADEMARKS, WASHINGTON, D.C. 20231  
APPLICANT AND/OR ATTORNEY REQUESTS THE DATE OF  
DEPOSIT AS THE FILE DATE.

DATE OF DEPOSIT:

8/8/01

BY SIGNATURE & DATE:

*Marshall M. Curtis* 8/8/01